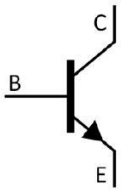
TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

P_C ,h_{FE} , 9015
High P_C and h_{FE} excellent h_{FE} linearity, complementary pair with 9015.

Low frequency, low noise amplifier.



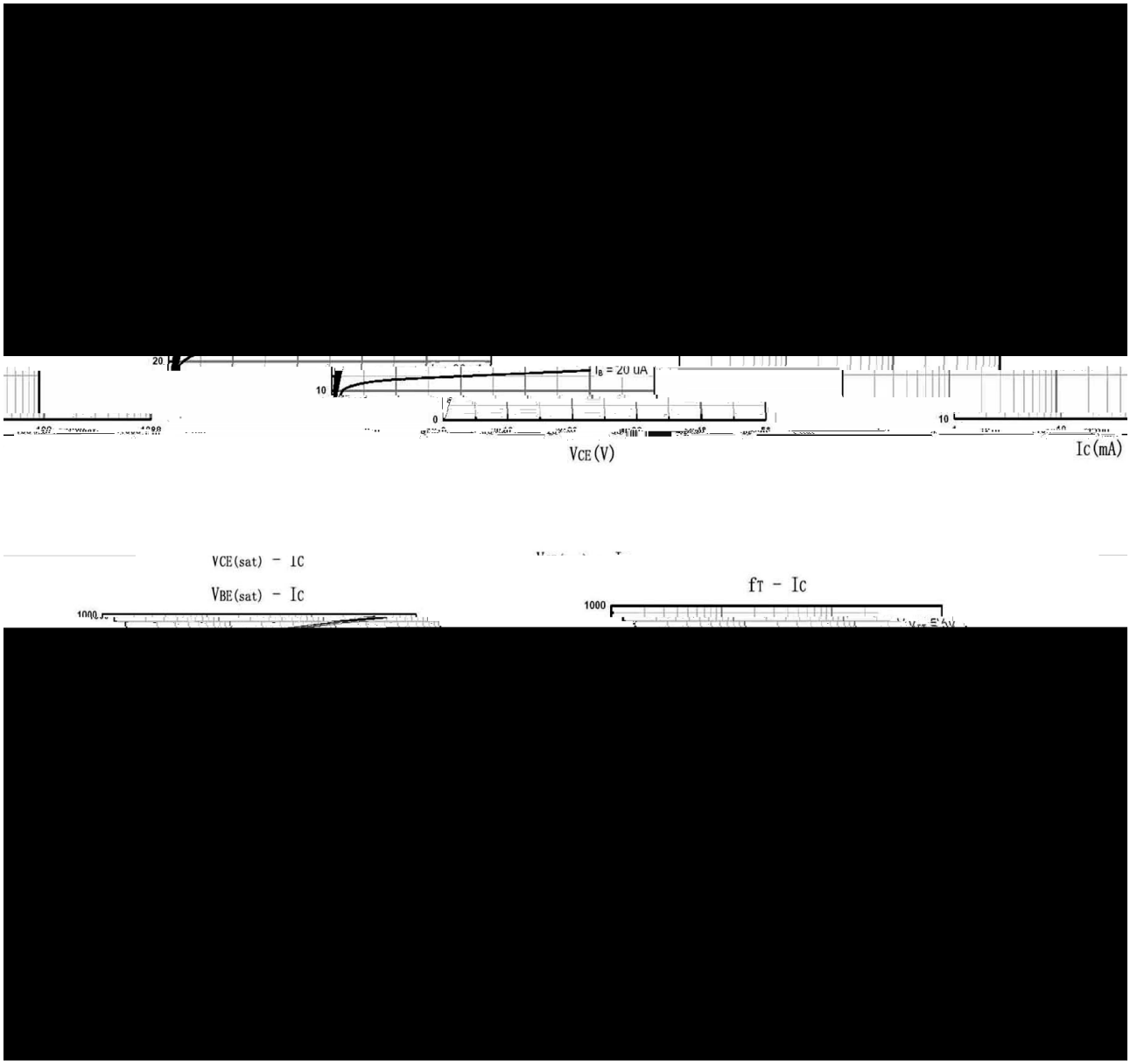


PIN1 Collector PIN 2 Base PIN 3 Emitter

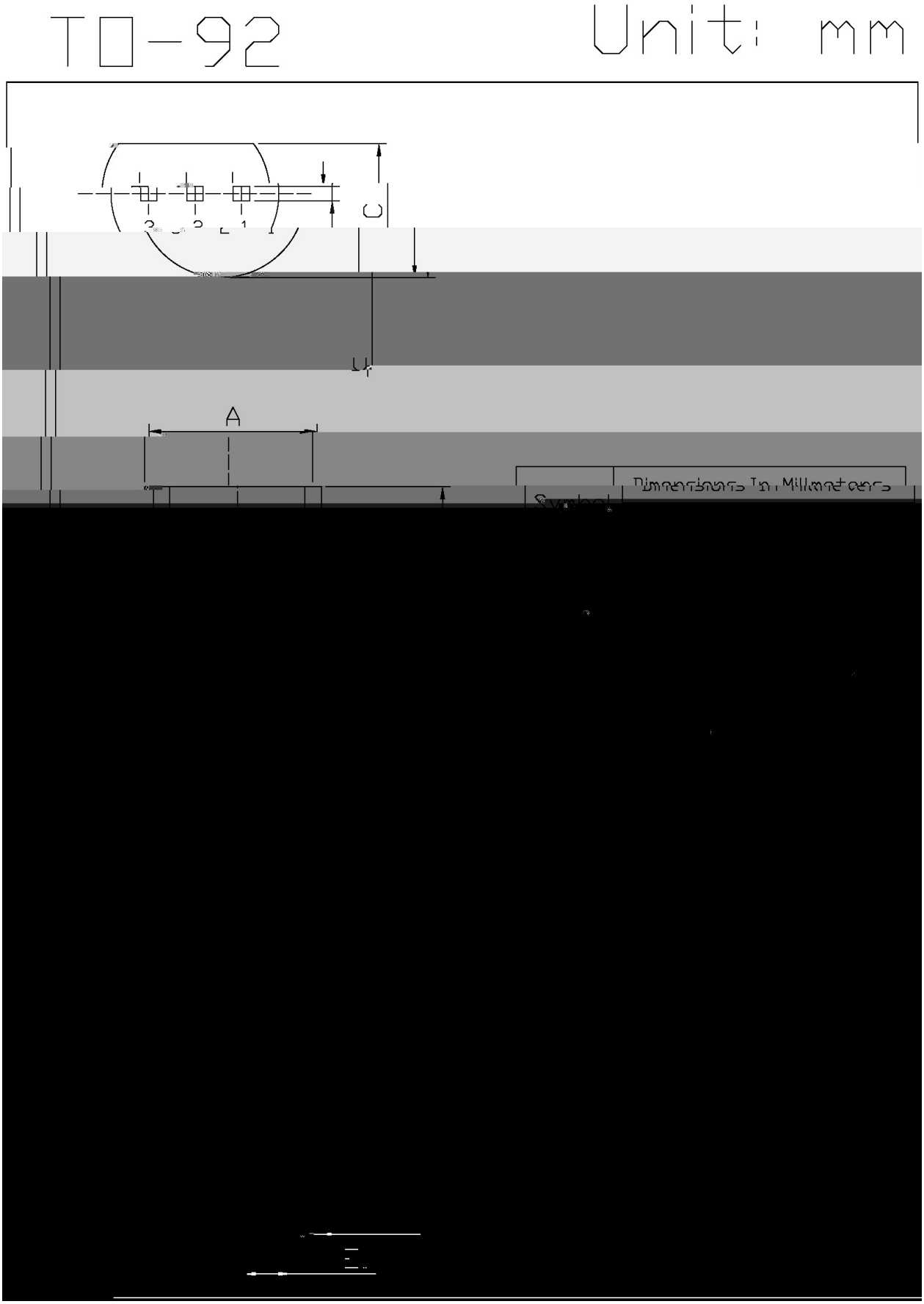
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	450	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA				

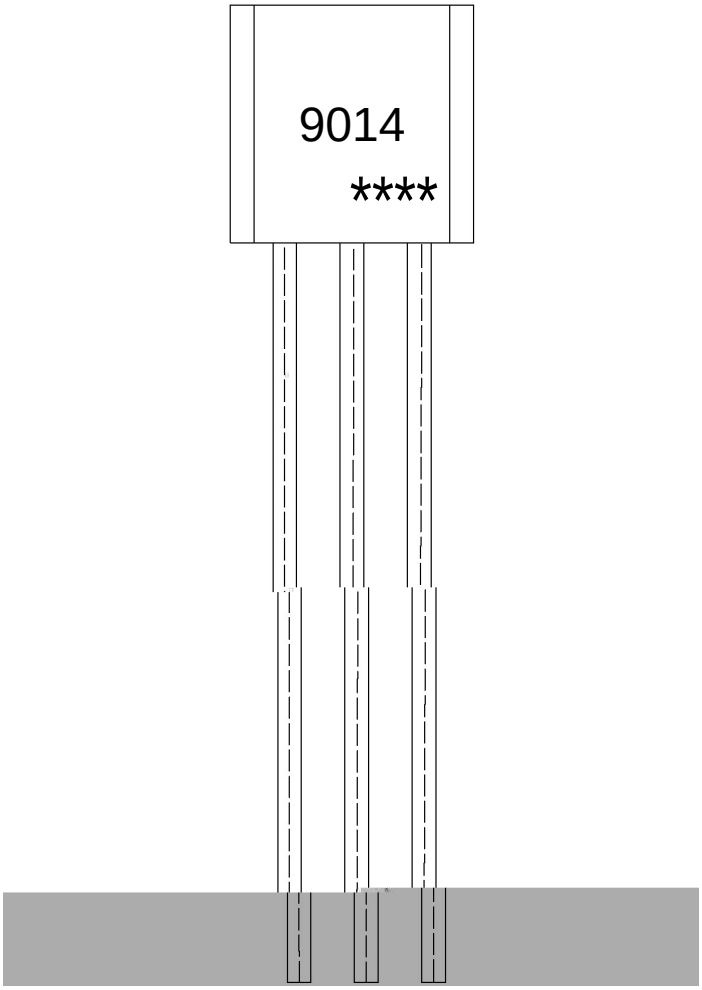
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

9014

A: h_{FE}

****

Note:

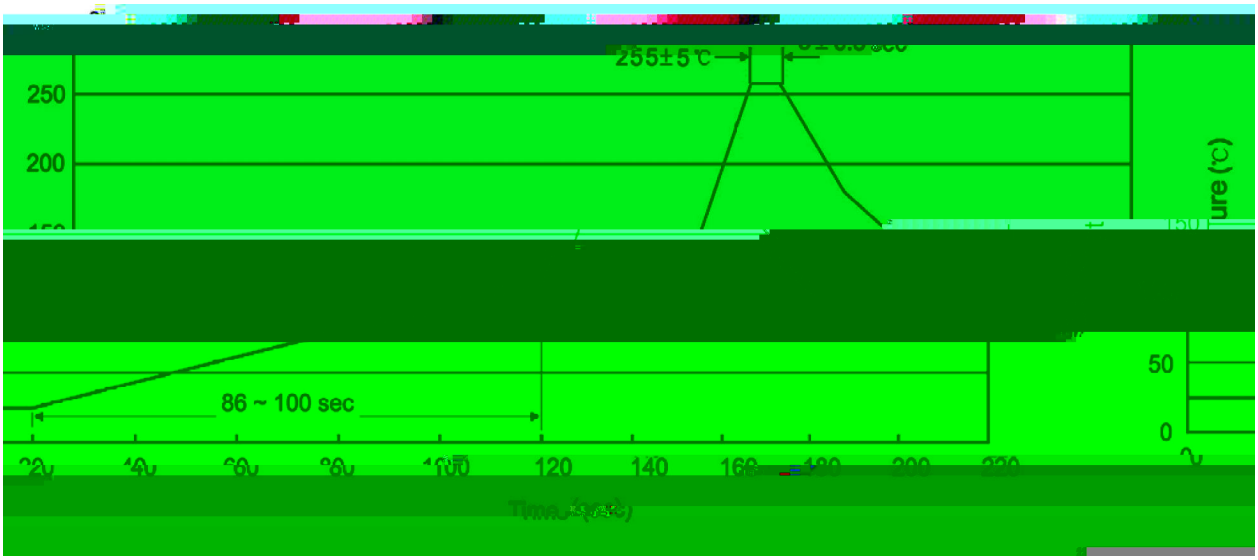
BR: Company Code.

9014: Product Type.

A: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



				Note:	
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

/ AMMO

Package Type	Units					Dimension	(unit mm3)
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92	3,000	1	120	10	30,000	328×230×42	480×346×235 547×407×268

/ Notices